

Victor Makhniy

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Luminescence of (ZnSe:Al):Yb Crystals at 4.2 K. Semiconductors, 2019, 53, 310-312.	0.5	0
2	Thermal Annealing Effect on Optical Properties of the Cadmium Telluride Films. Journal of Nano- and Electronic Physics, 2017, 9, 05047-1-05047-3.	0.5	2
3	OPTICAL PROPERTIES OF Cd _{0.55} Mn _{0.45} Te FILMS WITH NANO-SCALE SURFACE FORMATIONS. Telecommunications and Radio Engineering (English Translation of Elektrosvyaz and Radiotekhnika), 2017, 76, 865-871.	0.4	0
4	Preparation and Optical Properties of Substrates with Surface Nanostructure. Journal of Nano- and Electronic Physics, 2017, 9, 05026-1-05026-5.	0.5	0
5	Optoelectronic properties of InGaP diodes with a modified surface. Physica E: Low-Dimensional Systems and Nanostructures, 2016, 83, 227-231.	2.7	7
6	"PURIFICATION EFFECTS" IN ZINC SELENIDE CRYSTALS DOPED WITH YTTERBIUM FROM VAPOR PHASE. Telecommunications and Radio Engineering (English Translation of Elektrosvyaz and Radiotekhnika), 2016, 75, 279-284.	0.4	3
7	Optical properties of ZnSe(Te) with ytterbium impurity. Applied Optics, 2016, 55, B1.	1.8	0
8	Hall effect in CdTe crystals doped with Sn from the vapor phase. Semiconductors, 2014, 48, 1432-1433.	0.5	0
9	Optical absorption spectra as a useful tool to find parameters of deep impurity centers in semiconductors. Applied Optics, 2014, 53, B8.	1.8	1
10	Nature of the blue emission band in zinc selenide containing sulfur isovalent impurity. Semiconductors, 2014, 48, 1161-1162.	0.5	0
11	Preparation of InVI and IVaVI semiconductor films for solar cells by the isovalent substitution technique with a CBD-made substrate. Inorganic Materials, 2014, 50, 546-550.	0.8	11
12	±-CdTe LAYERS: GROWING AND OPTICAL PROPERTIES. Telecommunications and Radio Engineering (English Translation of Elektrosvyaz and Radiotekhnika), 2014, 73, 909-914.	0.4	0
13	PECULIARITIES OF THE OPTICAL PROPERTIES OF WIDE-GAP II-VI COMPOUNDS WITH Mg ISOVALENT IMPURITY. Telecommunications and Radio Engineering (English Translation of Elektrosvyaz and Radiotekhnika), 2014, 73, 909-914.	0.4	0
14	Effect of heat treatment on the surface parameters of cadmium-telluride single-crystal substrates. Journal of Surface Investigation, 2013, 7, 562-564.	0.5	2
15	PHYSICAL PROPERTIES OF ZnSe HETEROLAYERS OBTAINED BY ISOVALENT SUBSTITUTION. Telecommunications and Radio Engineering (English Translation of Elektrosvyaz and Radiotekhnika), 2013, 72, 1893-1897.	0.4	0
16	PHYSICAL PROPERTIES OF CdSe HETEROLAYERS WITH ISOVALENT TELLURIUM IMPURITY. Telecommunications and Radio Engineering (English Translation of Elektrosvyaz and Radiotekhnika), 2013, 72, 741-744.	0.4	0
17	Luminescence of broad-band compounds of elements of groups II-VI with a tin impurity. Journal of Optical Technology (A Translation of Opticheskiy Zhurnal), 2012, 79, 123.	0.4	0
18	Determination of the ionization energy of vanadium levels in zinc selenide. Semiconductors, 2012, 46, 141-142.	0.5	1

#	ARTICLE	IF	CITATIONS
19	UV PHOTOELECTRIC DETECTOR WITH INCORPORATED INTERNAL GAIN. Telecommunications and Radio Engineering (English Translation of Elektrosvyaz and Radiotekhnika), 2012, 71, 1381-1385.	0.4	0
20	Mechanism of ZnO heterolayer formation on ZnSe substrates. Inorganic Materials, 2011, 47, 746-748.	0.8	1
21	Mechanism of tin diffusion in ZnTe single crystals. Inorganic Materials, 2011, 47, 945-946.	0.8	3
22	UV detector with internal gain based on SnO ₂ -ZnSe heterostructure. Technical Physics Letters, 2011, 37, 354-355.	0.7	1
23	The nature of edge luminescence of CdTe:Mg diffusion layers. Semiconductors, 2010, 44, 1167-1169.	0.5	1
24	Effects of codoping in ZnO-based semimagnetic semiconductor thin films. IOP Conference Series: Materials Science and Engineering, 2010, 8, 012042.	0.6	1
25	OPTICAL PROPERTIES OF ZnSe:V CRYSTALS. Telecommunications and Radio Engineering (English) Tj ETQq1 1 0.784314 rgBT /Overlock 10 Tj ETQq1 1 0.784314 rgBT /Overlock 10	0.4	1
26	Luminescence of zinc oxide layers synthesized on zinc selenide substrates by the isovalent substitution method. Russian Physics Journal, 2009, 52, 216-217.	0.4	2
27	Semimagnetic semiconductor oxides as materials for transparent electronics and spintronics. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 2177-2181.	1.8	2
28	Perspective of surface modification of CdTe single crystal substrate for creation of photosensitive barrier structures. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2009, 12, 143-146.	1.0	3
29	Electrophysical Properties of Zinc Selenide Diffusion Layers Doped with 3-D Elements from the Vapor Phase. Telecommunications and Radio Engineering (English Translation of Elektrosvyaz and) Tj ETQq1 1 0.784314 rgBT /Overlock 10 Tj ETQq1 1 0.784314 rgBT /Overlock 10	0.4	1
30	Current transport mechanisms in n-CdSe/p-CdTe heterojunctions. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 3622-3625.	0.8	15
31	Formation and Properties of n-CdO/p-CdTe Heterojunction. Telecommunications and Radio Engineering (English Translation of Elektrosvyaz and Radiotekhnika), 2008, 67, 1763-1768.	0.4	0
32	<title>Surface-barrier sensors on basis of zinc selenide</title>. , 2007, , .		0
33	The origin of edge luminescence in diffusion ZnSe:Sn layers. Semiconductors, 2007, 41, 784-785.	0.5	3
34	Electrical Properties of Surface-Barrier Diodes Based on the CdTe Crystals with Modified Surface. Telecommunications and Radio Engineering (English Translation of Elektrosvyaz and Radiotekhnika), 2007, 66, 1769-1774.	0.4	1
35	Mechanisms of Defect Formation for ZnSe with Isovalent Oxygen Impurity. Telecommunications and Radio Engineering (English Translation of Elektrosvyaz and Radiotekhnika), 2007, 66, 465-471.	0.4	1
36	Defect Formation Mechanisms for ZnSe with Isovalent Oxygen Impurity. Telecommunications and Radio Engineering (English Translation of Elektrosvyaz and Radiotekhnika), 2007, 66, 1205-1211.	0.4	0

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37	FORMATION OF Ge NANOCRYSTALS BY ELECTRON BEAM EVAPORATION. , 2007, , .		0
38	<title>Semiconductor UV-radiation detectors for biology and medicine</title>. , 2006, 6254, 493.		0
39	Specific features of the physical properties of a modified CdTe surface. Semiconductors, 2005, 39, 792-794.	0.5	3
40	<title>Photodetectors on the base of CdTe and on the base of InSe for optical coherent tomography</title>. , 2004, , .		0
41	Green luminescence in diffusion-doped layers of zinc selenide. Technical Physics, 2004, 49, 798-799.	0.7	2
42	Electrical properties of UV detectors based on zinc selenide with modified surface barrier. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1039-1043.	0.8	1
43	Surface barrier diode based on zinc selenide with a passivating zinc oxide film. Technical Physics Letters, 2003, 29, 712-713.	0.7	2
44	Mechanisms of photocurrent generation in In ₂ O ₃ -InSe heterojunctions. Semiconductors, 2003, 37, 1387-1389.	0.5	1
45	Photodetectors Based on the Gallium Phosphide-Arsenide Heterojunctions Produced by Isovalent Substitution Method. Telecommunications and Radio Engineering (English Translation of Elektrosvyaz) Tj ETQq1 1 0.784314ogBT /O		
46	<title>II-VI compounds wide-band barrier detectors of He-Ne laser</title>. , 2002, , .		0
47	Electrical and photoelectrical behavior of Au/n-CdTe junctions. , 2001, 4413, 258.		0
48	Isovalent substitution: a perspective method of producing heterojunction optoelectrical devices. , 2001, 4425, 272.		7
49	Semiconductor detectors for the erythema region of UV radiation. , 1999, , .		1